



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

RB521S-30

## SOD-523 Schottky Barrier Diode 肖特基势垒二极管

### Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	RB521S-30
Pin 管脚	
Mark 打标	

### Absolute Maximum Ratings 最大额定值

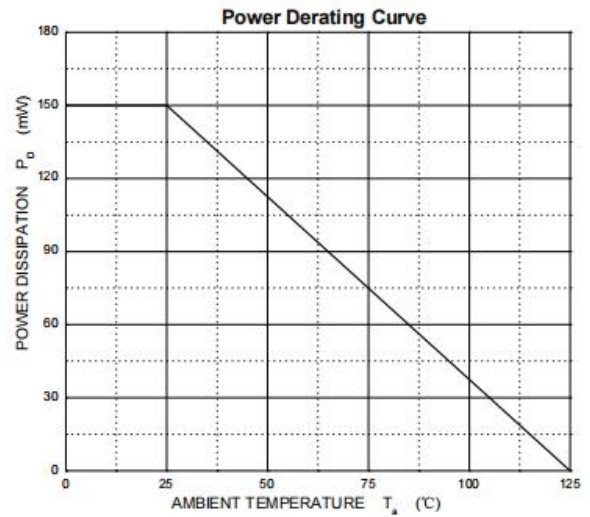
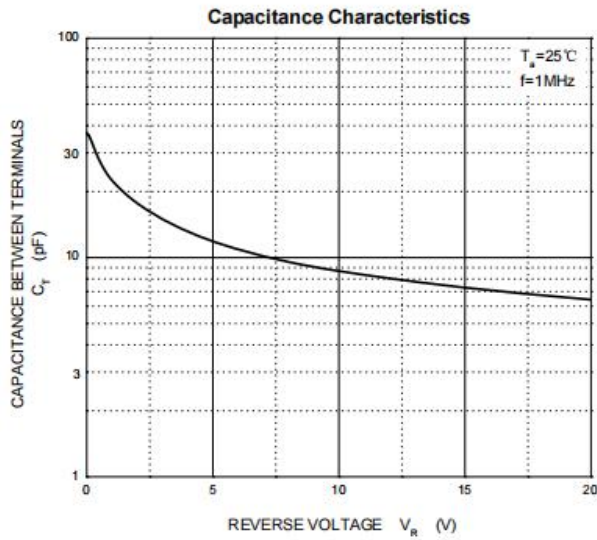
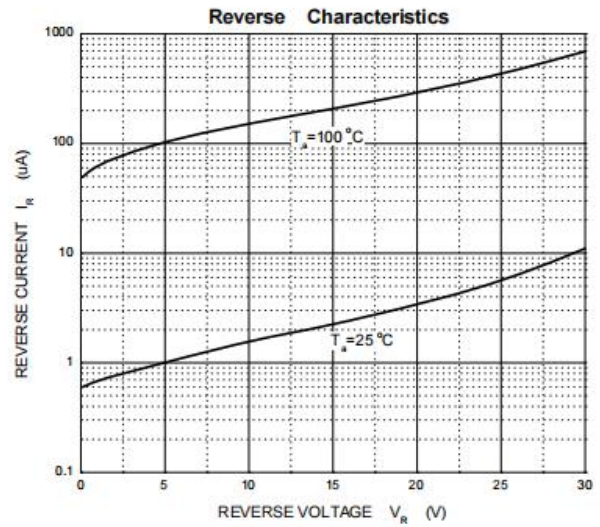
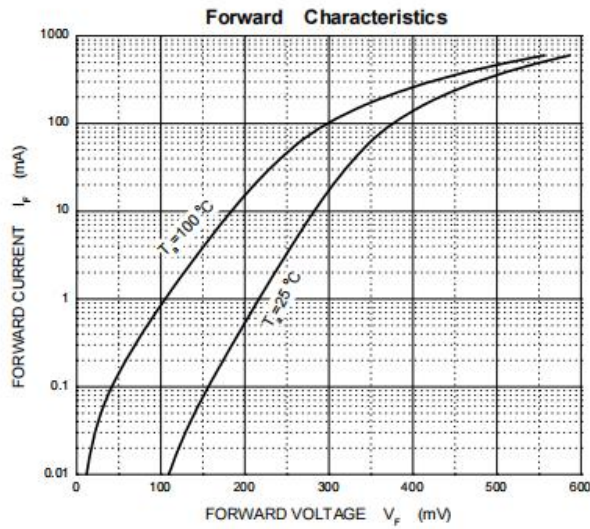
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
DC Reverse Voltage 直流反向电压	$V_R$	30	
Forward Work Current 正向工作电流	$I_o$	200	mA
Peak Forward Surge Current 正向峰值浪涌电流	$I_{FSM}$	1000	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+125 $^\circ C$	

### Electrical Characteristics 电特性

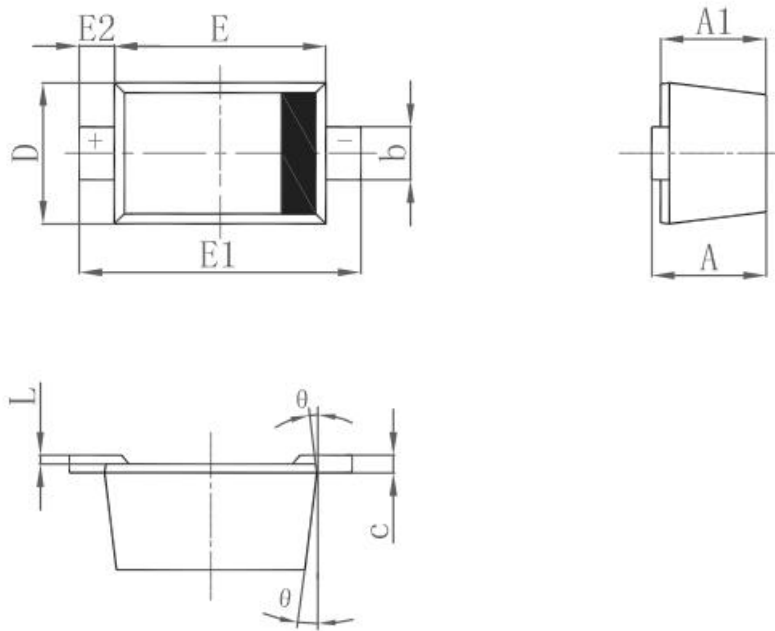
( $T_A=25^\circ C$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ C$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压( $I_R=100\mu A$ )	$V_{(BR)}$	30	—	V
Reverse Leakage Current 反向漏电流( $V_R=10V$ )	$I_R$	—	30	$\mu A$
Forward Voltage( $I_F=10mA$ ) 正向电压( $I_F=200mA$ )	$V_F$	—	0.35 0.5	V

## ■ Typical Characteristic Curve 典型特性曲线



## ■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
$\theta$	7° REF		7° REF	

单击下面可查看定价，库存，交付和生命周期等信息

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